



15V PNP MEDIUM POWER HIGH GAIN TRANSISTOR IN SOT223

Features

- BV_{CEO} > -15V
- BV_{CBO} > -15V
- I_C = -3A High Continuous Current
- h_{FE} > 300 @ -2A and Low Saturation Voltage
- Extremely Low Equivalent On-Resistance $R_{CE(sat)}$ 93m Ω at -3A
- Complementary NPN Type: DIODES™ FZT688B
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: SOT223
- Package Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads;
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

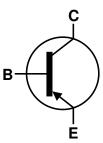
Applications

- Flash Gun Convertors
- Battery Powered Circuits

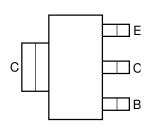




Top View



Device Symbol



Top View Pin-Out

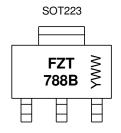
Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT788BTA	Standard	FZT788B	7	12	1,000
FZT788BTC	Standard	FZT788B	13	12	2,500

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



FZT 788B = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-15	V
Collector-Emitter Voltage	V_{CEO}	-15	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-3	Α
Peak Pulse Current	I _{CM}	-8	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3		
Power Dissipation	(Note 6)	D-	2	W	
Power Dissipation	(Note 7)	P _D	1.6		
	(Note 8)		1.2		
	(Note 5)		41.7		
Thermal Resistance, Junction to Ambient	(Note 6)	В	62.5		
Thermal nesistance, Junction to Ambient	(Note 7)	$R_{ hetaJA}$	78.1	°C/W	
	(Note 8)		104	1	
Thermal Resistance Junction to Lead (Note 9)		$R_{ hetaJL}$	12.9		
Operating and Storage Temperature Range	T_{J}, T_{STG}	-55 to +150	°C		

ESD Ratings (Note 10)

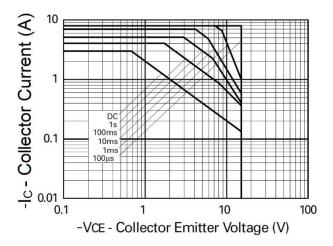
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	٧	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

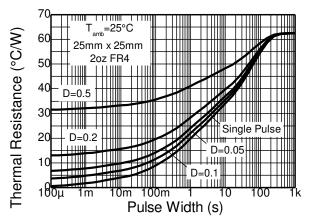
- 5. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
- 8. Same as Note 5, except the device is mounted on minimum recommended pad layout.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



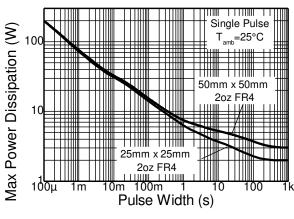
Thermal Characteristics and Derating Information



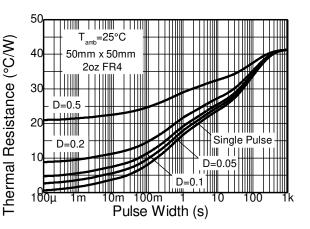
Safe Operating Area



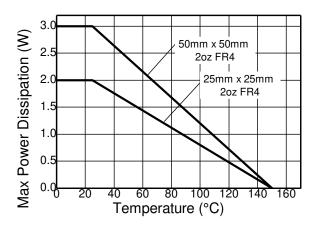
Transient Thermal Impedance



Pulse Power Dissipation



Transient Thermal Impedance



Derating Curve



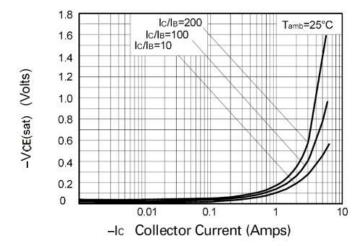
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

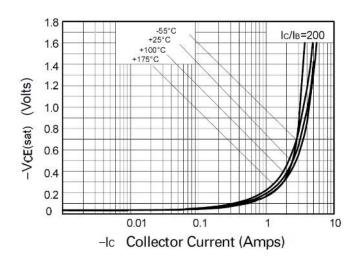
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	-15	_	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-15	_	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	_	_	V	I _E = -100μA
Collector-Base Cut-Off Current	I _{CBO}	_	_	-100	nA	V _{CB} = -10V
Emitter Cut-Off Current	I _{EBO}	_	_	-100	nA	V _{EB} = -4V
DC Current Gain (Note 11)	h _{FE}	500 400 300 150	_ _ _ _	_ _ _ _	_	$I_{C} = -10$ mA, $V_{CE} = -2$ V $I_{C} = -1$ A, $V_{CE} = -2$ V $I_{C} = -2$ A, $V_{CE} = -2$ V $I_{C} = -6$ A, $V_{CE} = -2$ V
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}		_ _ _	-0.15 -0.25 -0.45 -0.5	V	$I_C = -0.5A$, $I_B = -2.5mA$ $I_C = -1A$, $I_B = -5mA$ $I_C = -2A$, $I_B = -10mA$ $I_C = -3A$, $I_B = -50mA$
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	_	_	-0.9	V	$I_{C} = -1A, I_{B} = -5mA$
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	_	-0.75	_	V	I _C = -1A, V _{CE} = -2V
Input Capacitance	C _{ibo}	_	225	_	pF	V _{EB} = -0.5V, f = 1MHz
Output Capacitance	C _{obo}	_	25	_	pF	V _{CB} = -10V, f = 1MHz
Current Gain-Bandwidth Product	f _T	100	_	_	MHz	V _{CE} = -5V, I _C = -50mA, f=50MHz
Turn-On Time	ton		35		ns	V _{CC} = -10V, I _C = -500mA
Turn-Off Time	t _{off}	_	400	_	ns	$I_{B1} = -I_{B2} = -50 \text{mA}$

Note: 11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)



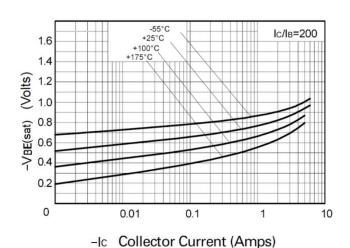


VCE(sat) v IC

+100°C VcE=-2V 1.6 +25°C 1200 -55°C 1.4 900 <u>B</u> 1.2 Typical 1.0 8.0 0.6 300 0.4 0.2 0 0.01 0.1 10

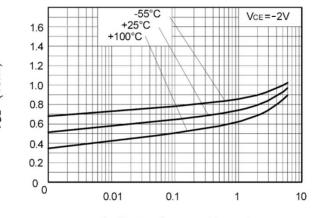
hFE - Normalised Gain

VCE(sat) v IC



-Ic Collector Current (Amps)

hFE v IC



-Ic Collector Current (Amps)

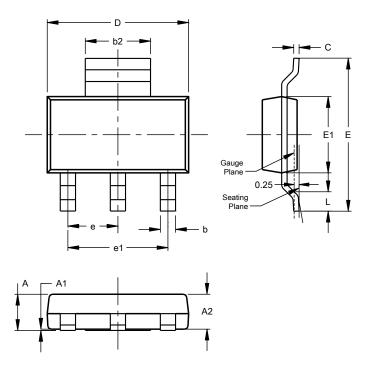
VBE(on) v IC

VBE(sat) v IC



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

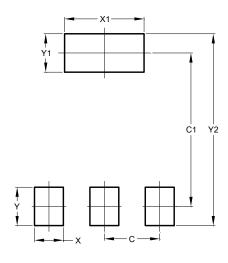


SOT223 (Type DN)				
Dim	Min	Max	Тур	
Α		1.70		
A1	0.01	0.15		
A2	1.50	1.68	1.60	
b	0.60	0.80	0.70	
b2	2.90	3.10		
С	0.20	0.32		
D	6.30	6.70		
Е	6.70	7.30		
E1	3.30	3.70		
е			2.30	
e1			4.60	
L	0.85			
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00



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